

HIGH VOLTAGE BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

TISP4600F3, **TISP4700F3**

Ion-Implanted Breakdown Region Precise and Stable Voltage Low Voltage Overshoot under Surge

| Device | V _{DRM} V | V _(BO) |
|--------|-----------------------|-------------------|
| '4600 | 420 | 600 |
| '4700 | 500 | 700 |

Rated for International Surge Wave Shapes

| Waya Chana | Cton dowl | I _{TSP} |
|------------|------------------------------|------------------|
| Wave Shape | Standard | Α |
| 2/10 | GR-1089-CORE | 190 |
| 8/20 | IEC 61000-4-5 | 175 |
| 10/160 | FCC Part 68 | 110 |
| 10/700 | FCC Part 68 ITU-T K.20/21 | 70 |
| 10/560 | FCC Part 68 | 50 |
| 10/1000 | GR-1089-CORE | 45 |



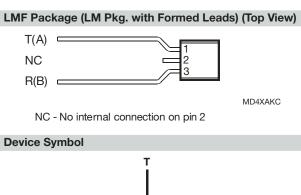
.....UL Recognized Component

Description

These devices are designed to limit overvoltages between a system and the protective ground. The TISP4700F3 is designed for insulation protection of systems such as LANs, and allows a float voltage of 500 V without clipping. IEC 60950 and UL 1950 have certain requirements for incoming lines of telephone network voltage (TNV). Any pro-

T(A) 1 2 3 MD4XATA

NC - No internal connection on pin 2





Terminals T and R correspond to the alternative line designators of A and B

tector from the line to ground must have a voltage rating of 1.6 times the equipment rated voltage. International and European equipment usually have maximum rated voltages of 230 V rms, 240 V rms or 250 V rms. Multiplying the 250 V value by 1.6 gives a protector V_{DRM} value of 400 V. Allowing for operation down to 0 °C gives a V_{DRM} value of 420 V at 25 °C. This need is met by the TISP4600F3.

The protector consists of a symmetrical voltage-triggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The high crowbar holding current prevents d.c. latchup as the diverted current subsides. A single device provides 2-point protection. Combinations of devices can be used for multipoint protection (e.g. 3-point protection between Ring, Tip and Ground).

The TISP4x00F3 is guaranteed to voltage limit and withstand the listed international lightning surges in both polarities. This protection device is in a DO-92 (LM) cylindrical plastic package.

How To Order

| Device | Package | Carrier | For Standard Termination Finish Order As | For Lead Free Termination Finish Order As |
|------------|-------------------------|---------------|--|---|
| TISP4x00F3 | LM, Straight Lead DO-92 | Bulk Pack | TISP4x00F3LM | TISP4x00F3LM-S |
| TISP4x00F3 | LM, Straight Lead DO-92 | Tape And Reel | TISP4x00F3LMR | TISP4x00F3LMR-S |
| TISP4x00F3 | LMF, Formed Lead DO-92 | Tape And Reel | TISP4x00F3LMFR | TISP4x00F3LMFRS |

Insert x = 6 for TISP4600F3 and x = 7 for TISP4700F3

TISP4600F3, TISP4700F3

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Absolute Maximum Ratings, $T_A = 25$ °C (Unless Otherwise Noted)

| Rating | Symbol | Value | Unit |
|--|--------|----------------|------|
| Repetitive peak off-state voltage TISP4600F3 TISP4700F3 | | ± 420 ± 500 | V |
| Non-repetitive peak on-state pulse current (see Notes 1 and 2) | | | |
| 2/10 (Telcordia GR-1089-CORE, 2/10 voltage wave shape) | | 190 | |
| 1/20 (ITU-T K.22, 1.2/50 voltage wave shape, 25 Ω resistor) | | 100 | |
| 8/20 (IEC 61000-4-5, combination wave generator, 1.2/50 voltage wave shape) | | 175 | |
| 10/160 (FCC Part 68, 10/160 voltage wave shape) | | 110 | |
| 4/250 (ITU-T K.20/21, 10/700 voltage wave shape, simultaneous) 5/310 (ITU-T K.20/21, 10/700 voltage wave shape, single) 5/320 (FCC Part 68, 9/720 voltage wave shape, single) 10/560 (FCC Part 68, 10/560 voltage wave shape) | | 95 | A |
| | | 70 | ı |
| | | 70 | |
| | | 50 | |
| 10/1000 (Telcordia GR-1089-CORE, 10/1000 voltage wave shape) | | 45 | |
| Non-repetitive peak on-state current (see Notes 1 and 2) | | 6 | |
| 50/60 Hz, 1 s | | 6 | Α |
| Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A | | 250 | A/μs |
| Junction temperature | TJ | -40 to +150 | °C |
| Storage temperature range | | -65 to +150 | °C |

NOTES: 1. Initially, the TISP must be in thermal equilibrium with T_J = 25 °C.

Recommended Operating Conditions

| | Component | | | Max | Unit |
|--------|---|----|--|-----|------|
| | Series resistor for GR-1089-CORE first-level surge survival | 15 | | | |
| R1, R2 | Series resistor for ITU-T recommendation K.20 and K.21 | 0 | | | 0 |
| nı, nz | Series resistor for FCC Part 68 9/720 survival | 0 | | | 52 |
| | Series resistor for FCC Part 68 10/160, 10/560 survival | 10 | | | |

Electrical Characteristics, T_A = 25 $^{\circ}$ C (Unless Otherwise Noted)

| | Parameter | Test Conditions | | Min | Тур | Max | Unit |
|-------------------|--|---|--|-------|----------|--------------|-------|
| I _{DRM} | Repetitive peak off- state current | $V_D = \pm V_{DRM}$ | | | | ±5 | μΑ |
| V _(BO) | Breakover voltage | $IV/dt = \pm 700 \text{ V/ms}, R_{SOURCE} = 300 \Omega$ TISP4600F3 TISP4700F3 | | | | ±600 ±700 | V |
| I _(BO) | Breakover current | $dv/dt = \pm 700 \text{ V/ms}, R_{SOURCE} = 300 \Omega$ | | | ±0.1 | | Α |
| I _H | Holding current | $T = \pm 5 \text{ A}, \text{ di/dt} = \pm -30 \text{ mA/ms}$ | | ±0.15 | | | Α |
| dv/dt | Critical rate of rise of off-state voltage | Linear voltage ramp, Maximum ramp value < 0.85V _{DRM} | | ±5 | | | kV/μs |
| I _D | Off-state current | V _D = ±50 V | | | | ±10 | μΑ |
| C _{off} | Off-state capacitance | $f = 100 \text{ kHz}, V_d = 1 \text{ V rms}, V_D = 0,$ $f = 100 \text{ kHz}, V_d = 1 \text{ V rms}, V_D = -50 \text{ V}$ | | | 44 11 | 74 20 | pF |

^{2.} These non-repetitive rated currents are peak values of either polarirty. The surge may be repeated after the TISP returns to its initial conditions.

Thermal Characteristics

| Para | ameter | Test Conditions | Min | Тур | Max | Unit |
|--|--|---|-----|-----|------|------|
| | EIA/JESD51-3 PCB, $I_T = I_{TSM(1000)}$, $T_A = 25$ °C, (see Note 3) | | | 120 | °C/W | |
| $R_{\theta JA}$ Junction to free air t | | 265 mm x 210 mm populated line card, 4-layer PCB, I _T = I _{TSM(1000)} , T _A = 25 °C | | 57 | | O/VV |

NOTE 3: EIA/JESD51-2 environment and PCB has standard footprint dimensions connected with 5 A rated printed wiring track widths.

Parameter Measurement Information

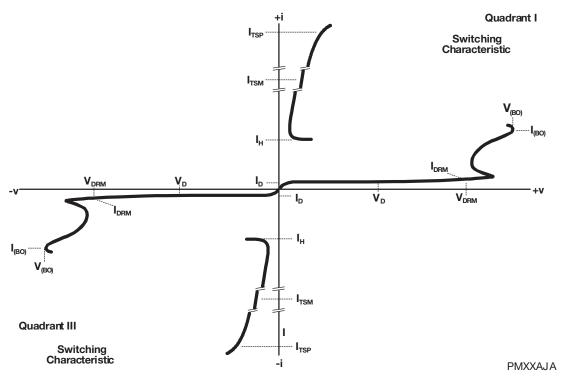
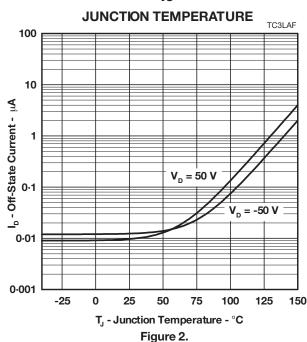


Figure 1. Voltage-Current Characteristic for R-T Terminal Pair

Typical Characteristics

OFF-STATE CURRENT

VS



NORMALIZED BREAKOVER VOLTAGE

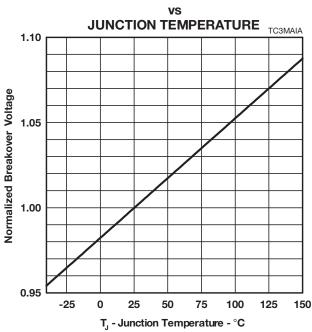
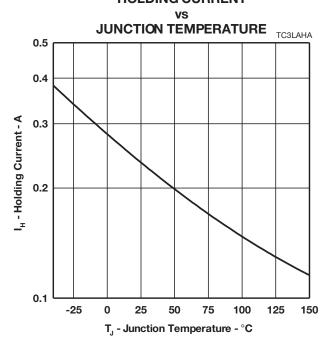


Figure 3.

HOLDING CURRENT



Thermal Information

NON-REPETITIVE PEAK ON-STATE CURRENT

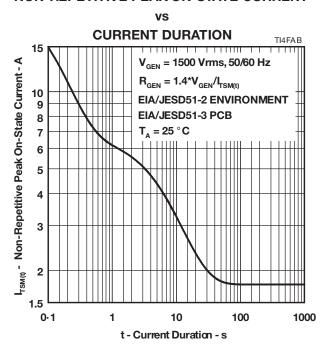


Figure 5.

APPLICATIONS INFORMATION

IEC 60950, EN 60950, UL 1950 and CSA 22.2 No.950

The '950 family of standards have certain requirements for equipment (EUT) with incoming lines of telecommunication network voltage (TNV). Any protector from a TNV conductor to protective ground must have a voltage rating of at least 1.6 times the equipment rated supply voltage (Figure 6). The intent is to prevent the possibility of the a.c. mains supply voltage from feeding into the telecommunication network and creating a safety hazard. International and European equipment usually have maximum rated voltages of 230 V rms, 240 V rms or 250 V rms. Multiplying the 250 V value by 1.6 gives a protector VDRM value of 400 V. Allowing for operation down to 0 °C gives a VDRM requirement of 420 V at 25 °C. This need is met by the TISP4600F3.

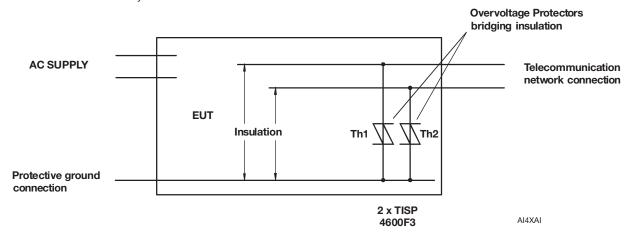


Figure 6. '950 TNV Network Insulation from Protective Ground

LAN Insulation Protection

In Figure 7, a low-voltage protector, Th1, from the TISP40xxL1 series limits the inter-conductor voltage of the LAN and the high-voltage protector, Th2, limits the insulation stress to 700 V. The four diode bridge, D1 through D4, reduces the capacitive loading of the protectors on the LAN and means that only one TISP4700F3 is needed to be used for insulation protection of both LAN conductors. Low voltage diodes can be used as the maximum reverse voltage stress is limited to the V_(BO) value of the TISP40xxL1 protector plus the diode forward recovery voltage.

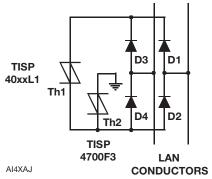


Figure 7. LAN Protection

TISP4600F3, TISP4700F3

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MECHANICAL DATA

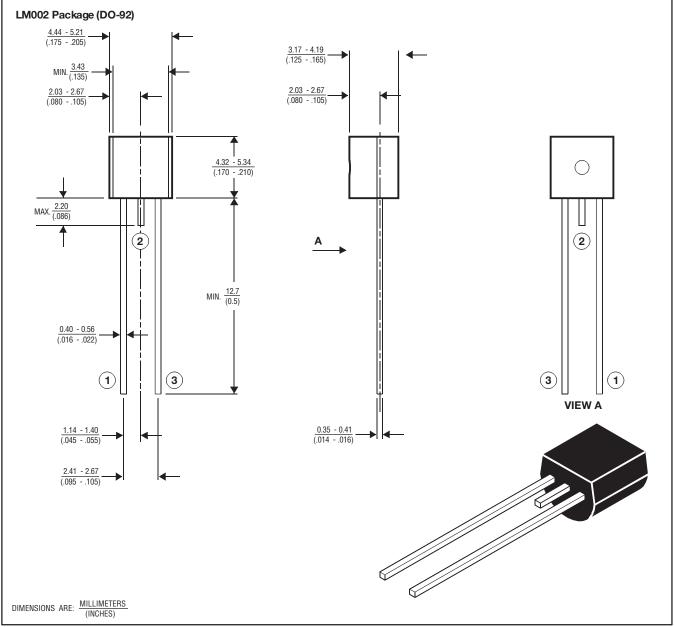
Device Symbolization Code

Devices will be coded as follows:

| Device | Symbolization Code |
|------------|-----------------------|
| TISP4600F3 | 4600F3 |
| TISP4700F3 | 4700F3 |

LM002 (DO-92) 2-Pin Cylindrical Plastic Package

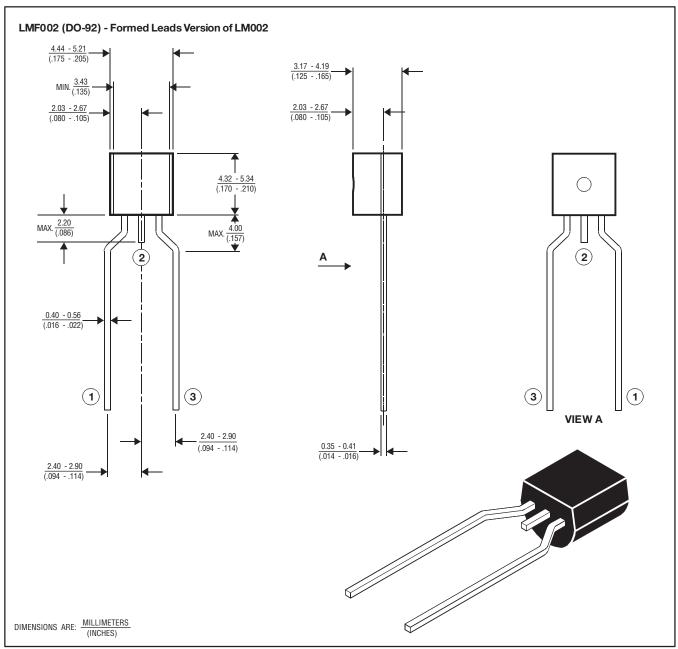
This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



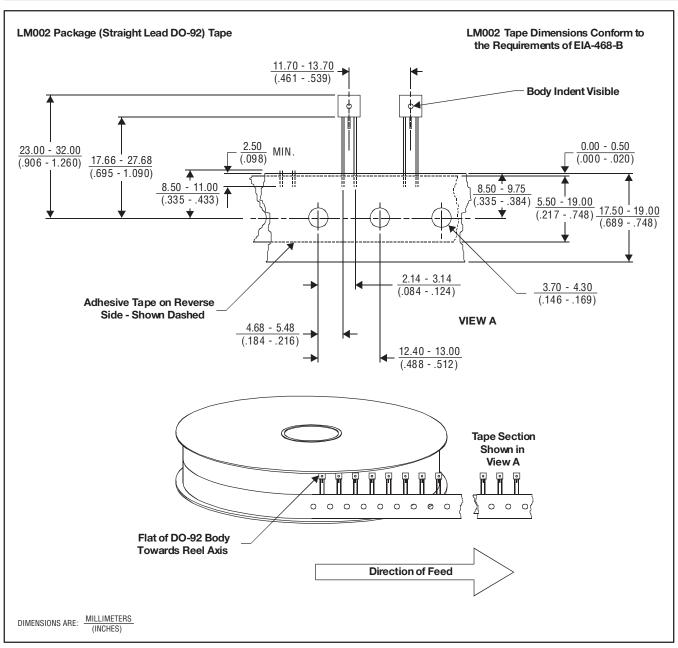
MD4XARA

LM002 (DO-92) - Formed Leads Version - 2-Pin Cylindrical Plastic Package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.

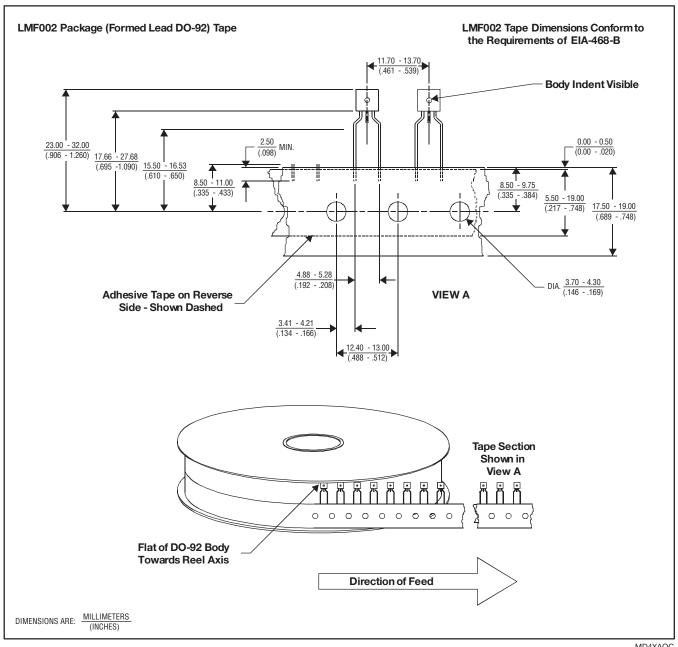


LM Tape Dimensions



MD4X APD

LMF Tape Dimensions



MD4XAQC

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